Preparation and Study of Heterojunctions Based on Chalcogenide Glassy Semiconductors

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Four types of heterojunctions were prepared: \(\text{SnO}_2\text{As}_2(\text{Se}_{0.9}\text{Te}_{0.1})_3\), \(\text{SnO}_2(\text{As}_{0.67}\text{Sb}_{0.33})_2\text{Se}_3\), n-GaAs-As\text{}\textsuperscript{2}Se\text{}\textsuperscript{3} and n-GaAs-As\text{}\textsuperscript{2}S\text{}\textsuperscript{3}. For all samples I-V characteristics and photosensitivity spectra were obtained. These heterostructures can be used for manufacturing rectifying devices and photoreceivers.

\textit{Key words:} Heterostructure; Chalcogenide Glassy Semiconductor; Spectra of Photosensitivity.